ASI SD1537-2

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI SD1537-2** is a Common Base Device Class C, Designed for IFF Applications.

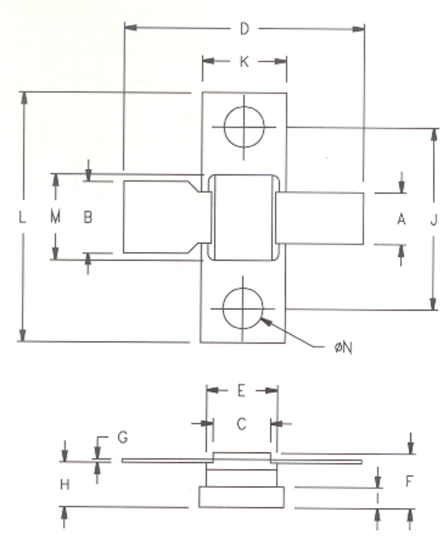
FEATURES INCLUDE:

- Gold Metelization
- InputMatching
- Broad Band Performance

MAXIMUM RATINGS

I_C	5.0 A
V_{CES}	50 V
P_{DISS}	300 W @ T_C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +150 °C
θ_{JC}	0.60 °C/W

PACKAGE STYLE .175 2L FLG



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.165/4,19	.175/4,45	J	.560/14,22	.570/14,48
B	.215/5,46	.225/5,72	K	.245/6,22	.255/6,48
C	.175/4,45	.185/4,70	L	.740/18,80	.750/19,05
D	.740/18,80		M	.245/6,22	.255/6,48
E	.225/5,72	.235/5,97	N	.128/3,25	.132/3,35
F	.155/3,94	.175/4,45			
G	.003/0,08	.006/0,15			
H	.120/3,05	.135/3,43			
I	.058/1,47	.068/1,73			

CHARACTERISTICS T_C = 25°C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 15 mA	50			**V**
BV_{EBO}	I_E = 10 mA	4.0			**V**
h_{FE}	V_{CE} = 5.0 V I_C = 200 mA	10			**---**
P_{OUT} **G_P** η_C	V_{CC} = 43 V P_{IN} = 20 W f = 1090 MHz PULSE WIDTH = 10 µS DUTY CYCLE = 1.0%	150 8.7 35			**W** **dB** **%**

A D V A N C E D S E M I C O N D U C T O R, I N C.

REV. A

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